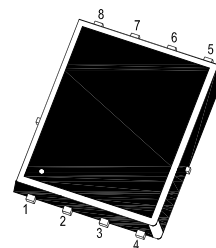
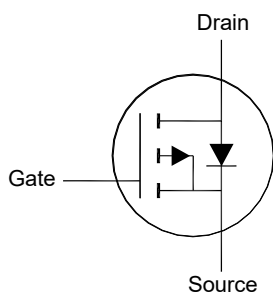


WTM503P300LS-HAF

P-Channel Enhancement Mode MOSFET

Features

- Logic level
- Low gate charge for fast power switching
- Halogen and Antimony Free(HAF), RoHS compliant



1. Source 2. Source 3. Source 4. Gate
5. Drain 6. Drain 7. Drain 8. Drain
DFN5060 Plastic Package

Applications

- Load Switch
- Motor Drives

Key Parameters

Parameter	Value	Unit
$-BV_{DSS}$	30	V
$R_{DS(ON)}$ Max	30 @ $-V_{GS} = 10$ V	m Ω
	45 @ $-V_{GS} = 4.5$ V	m Ω
$-V_{GS(th)}$ typ	1.8	V
Q_g typ	19.8 @ $-V_{GS} = 10$ V	nC

Absolute Maximum Ratings (at $T_a = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$-V_{DS}$	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current	$-I_D$	$T_c = 25^\circ\text{C}$	22
		$T_c = 100^\circ\text{C}$	14
Peak Drain Current, Pulsed ¹⁾	$-I_{DM}$	80	A
Single Pulse Avalanche Current	$-I_{AS}$	24	A
Single Pulse Avalanche Energy ²⁾	E_{AS}	28.8	mJ
Power Dissipation	P_D	20.8	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Max.	Unit
Thermal Resistance from Junction to Case	$R_{\theta JC}$	6	$^\circ\text{C}/\text{W}$
Thermal Resistance from Junction to Ambient ³⁾	$R_{\theta JA}$	50	$^\circ\text{C}/\text{W}$

¹⁾ Pulse Test: Pulse Width ≤ 100 μs , Duty Cycle $\leq 2\%$, Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)} = 150^\circ\text{C}$.

²⁾ Limited by $T_{J(MAX)}$, starting $T_J = 25^\circ\text{C}$, $L = 0.1$ mH, $R_g = 25$ Ω , $I_D = 24$ A, $V_{GS} = 10$ V.

³⁾ Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate in still air.

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Characteristics at $T_a = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit
STATIC PARAMETERS					
Drain-Source Breakdown Voltage at $-I_D = 250 \mu\text{A}$	$-BV_{DSS}$	30	-	-	V
Drain-Source Leakage Current at $-V_{DS} = 24 \text{ V}$	$-I_{DSS}$	-	-	1	μA
Gate Source Leakage Current at $V_{GS} = \pm 20 \text{ V}$	I_{GSS}	-	-	± 100	nA
Gate-Source Threshold Voltage at $V_{DS} = V_{GS}$, $-I_D = 250 \mu\text{A}$	$-V_{GS(th)}$	1.2	-	2.5	V
Drain-Source On-State Resistance at $-V_{GS} = 10 \text{ V}$, $-I_D = 10 \text{ A}$ at $-V_{GS} = 4.5 \text{ V}$, $-I_D = 5 \text{ A}$	$R_{DS(on)}$	- -	23 -	30 45	$\text{m}\Omega$
DYNAMIC PARAMETERS					
Gate resistance at $V_{DS} = 0 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 1 \text{ MHz}$	R_g	-	5	-	Ω
Forward Transconductance at $-V_{DS} = 5 \text{ V}$, $-I_D = 10 \text{ A}$	g_{fs}	-	15	-	S
Input Capacitance at $V_{GS} = 0 \text{ V}$, $-V_{DS} = 20 \text{ V}$, $f = 1 \text{ MHz}$	C_{iss}	-	1150	-	pF
Output Capacitance at $V_{GS} = 0 \text{ V}$, $-V_{DS} = 20 \text{ V}$, $f = 1 \text{ MHz}$	C_{oss}	-	103	-	pF
Reverse Transfer Capacitance at $V_{GS} = 0 \text{ V}$, $-V_{DS} = 20 \text{ V}$, $f = 1 \text{ MHz}$	C_{rss}	-	80	-	pF
Total Gate Charge at $-V_{DS} = 15 \text{ V}$, $-I_D = 10 \text{ A}$, $-V_{GS} = 10 \text{ V}$ at $-V_{DS} = 15 \text{ V}$, $-I_D = 10 \text{ A}$, $-V_{GS} = 4.5 \text{ V}$	Q_g	- -	19.8 10	- -	nC
Gate Source Charge at $-V_{DS} = 15 \text{ V}$, $-I_D = 10 \text{ A}$, $-V_{GS} = 10 \text{ V}$	Q_{gs}	-	3.6	-	nC
Gate Drain Charge at $-V_{DS} = 15 \text{ V}$, $-I_D = 10 \text{ A}$, $-V_{GS} = 10 \text{ V}$	Q_{gd}	-	3.8	-	nC
Turn-On Delay Time at $-V_{DS} = 15 \text{ V}$, $-V_{GS} = 10 \text{ V}$, $-I_D = 10 \text{ A}$, $R_g = 3.3 \Omega$	$t_{d(on)}$	-	9.3	-	nS
Turn-On Rise Time at $-V_{DS} = 15 \text{ V}$, $-V_{GS} = 10 \text{ V}$, $-I_D = 10 \text{ A}$, $R_g = 3.3 \Omega$	t_r	-	31	-	nS
Turn-Off Delay Time at $-V_{DS} = 15 \text{ V}$, $-V_{GS} = 10 \text{ V}$, $-I_D = 10 \text{ A}$, $R_g = 3.3 \Omega$	$t_{d(off)}$	-	14	-	nS
Turn-Off Fall Time at $-V_{DS} = 15 \text{ V}$, $-V_{GS} = 10 \text{ V}$, $-I_D = 10 \text{ A}$, $R_g = 3.3 \Omega$	t_f	-	2.8	-	nS
Body-Diode PARAMETERS					
Drain-Source Diode Forward Voltage at $-I_S = 1 \text{ A}$	$-V_{SD}$	-	0.8	1.2	V
Body Diode Reverse Recovery Time at $-I_S = 10 \text{ A}$, $di/dt = 100 \text{ A} / \mu\text{s}$	t_{rr}	-	9.8	-	nS
Body Diode Reverse Recovery Charge at $-I_S = 10 \text{ A}$, $di/dt = 100 \text{ A} / \mu\text{s}$	Q_{rr}	-	4.1	-	nC

Electrical Characteristics Curves

Fig.1 Output Characteristic

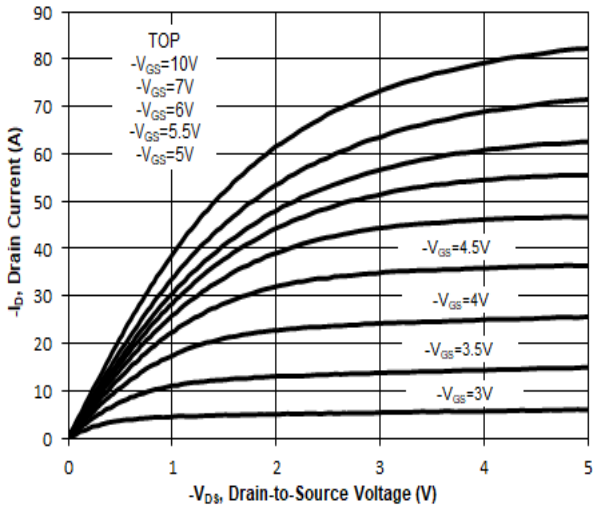


Fig.2 Transfer Characteristic

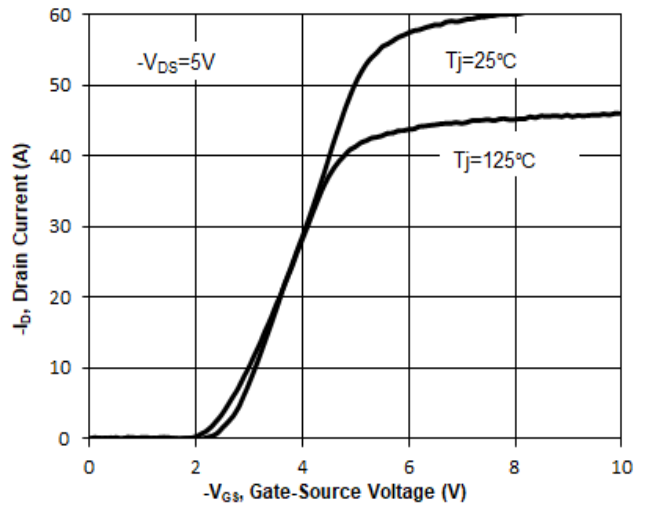


Fig.3 On Resistance vs. Gate-Source

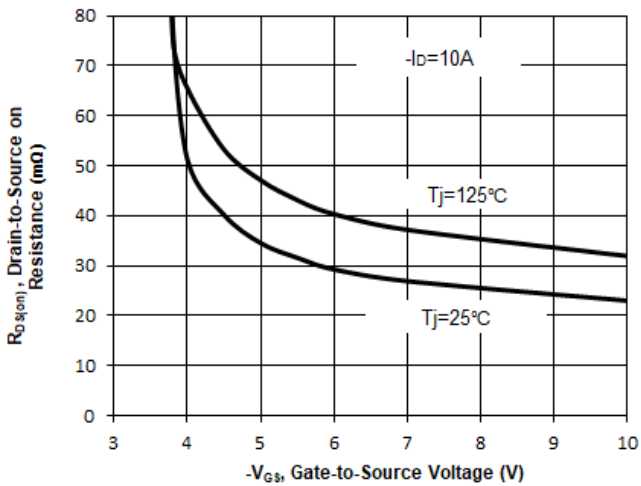


Fig.4 On Resistance vs. Temperature

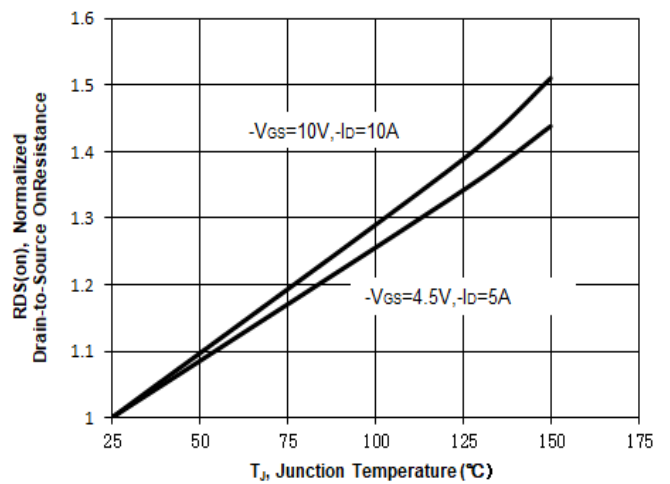


Fig.5 on Resistance vs. Drain Current

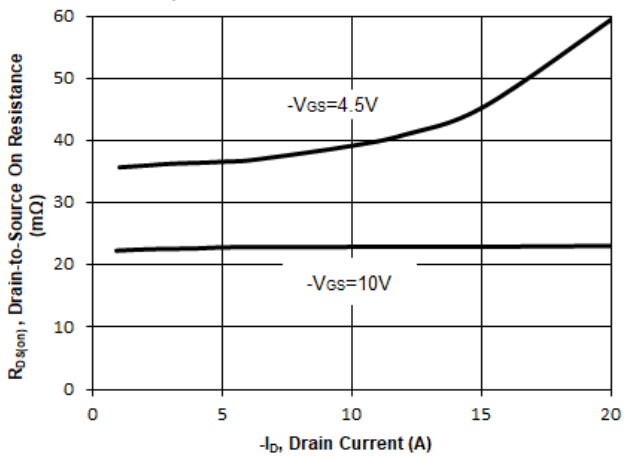
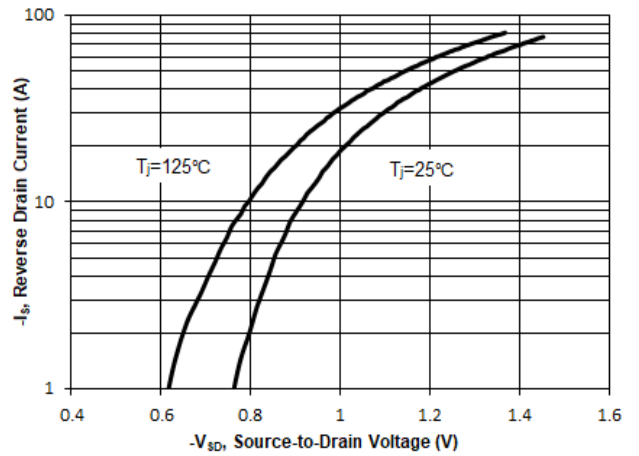


Fig.6 Source-Drain Diode Forward



WTM503P300LS-HAF

Electrical Characteristics Curves

Fig.7 Drain Leakage Current Vs Tj

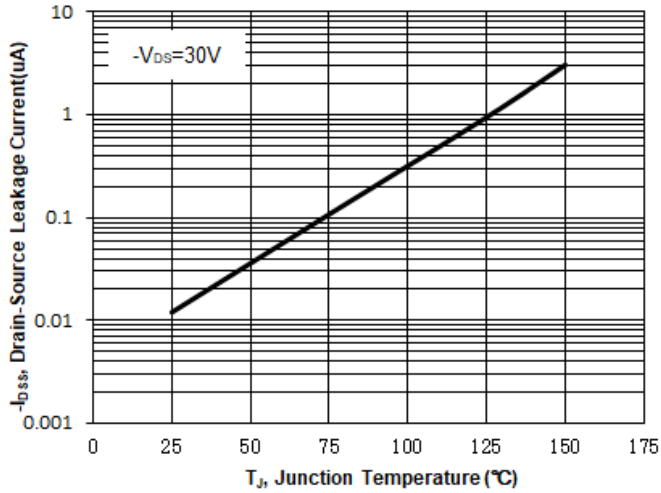


Fig.8 Drain-Source Breakdown Voltage Vs Tj

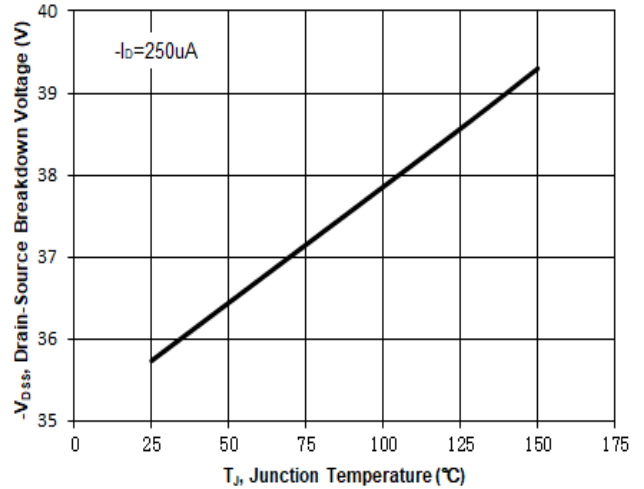


Fig.9 Gate-Source Threshold Voltage Vs Tj

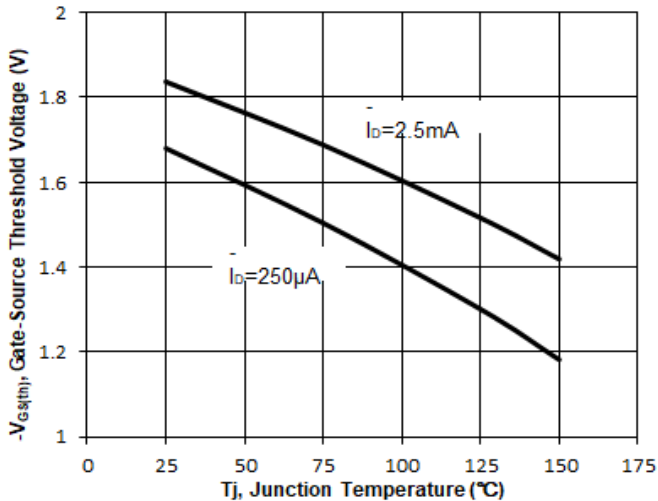


Fig.10 Capacitance Characteristic vs. on Resistance

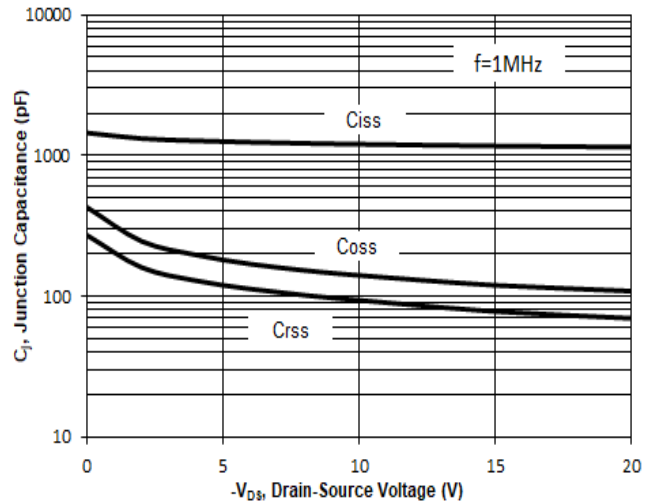


Fig.11 Gate Charge Characteristic

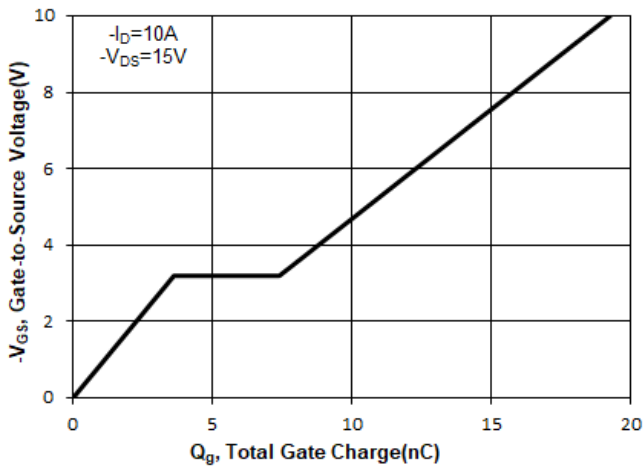
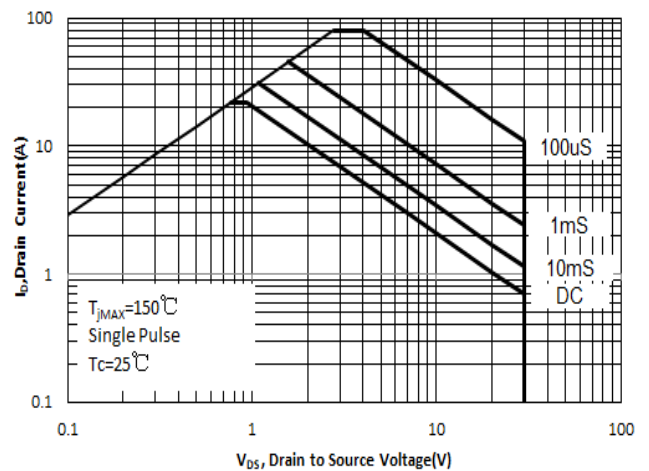


Fig.12 SOA, Safe Operating Area



Electrical Characteristics Curves

Fig.13 Normalized Maximum Transient Thermal Impedance($Z_{\theta JA}$)

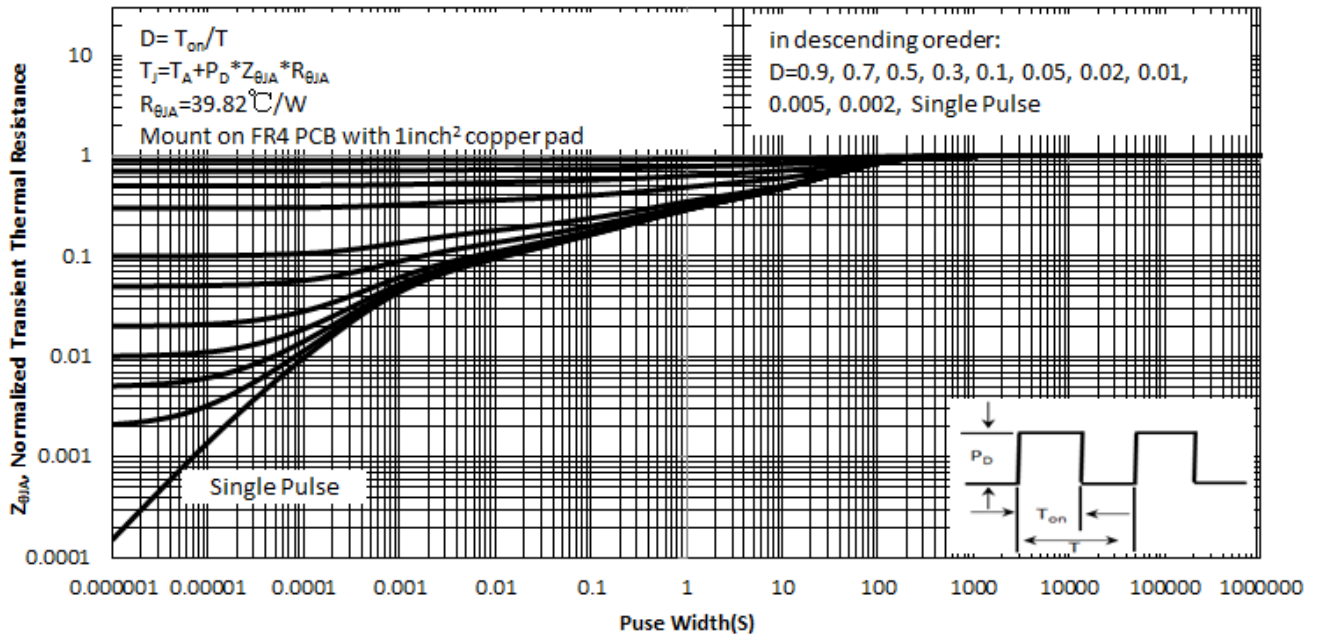
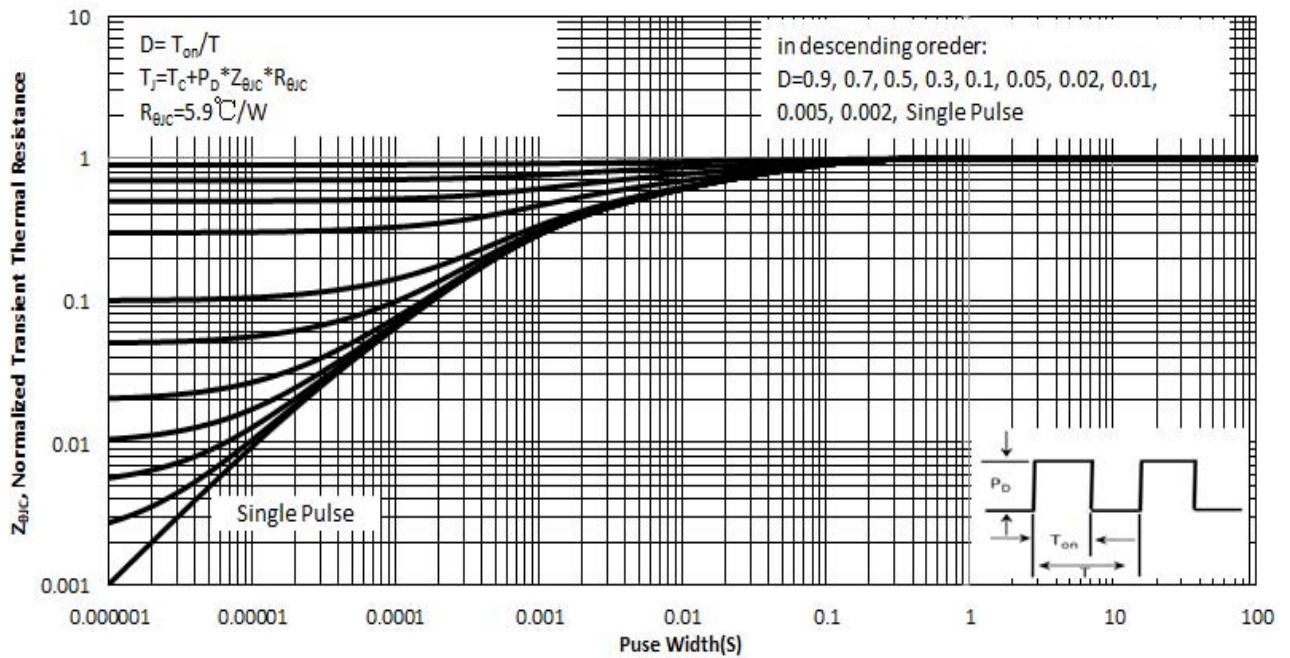


Fig.14 Normalized Maximum Transient Thermal Impedance($Z_{\theta JC}$)



Test Circuits

Fig.1-1 Switching times test circuit

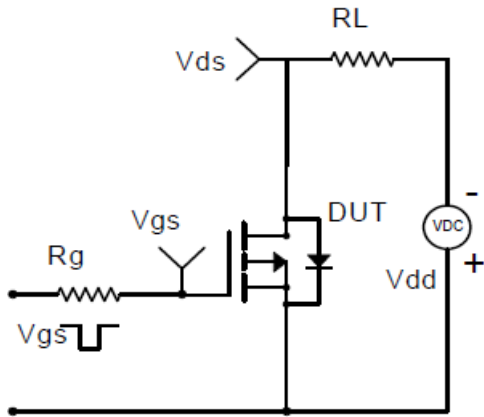


Fig.1-2 Switching Waveform

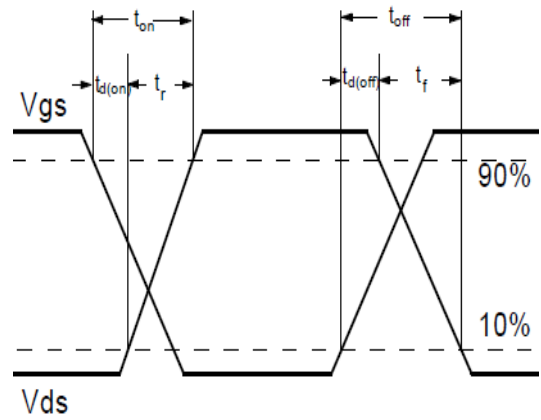


Fig.2-1 Gate charge test circuit

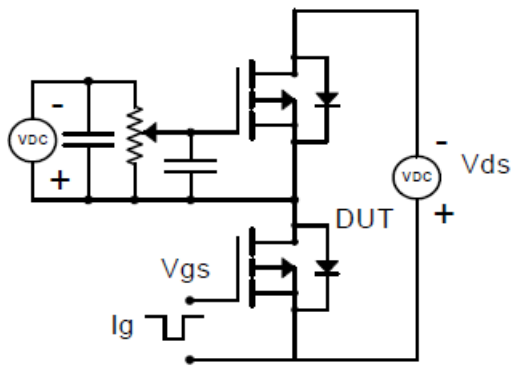


Fig.2-2 Gate charge waveform

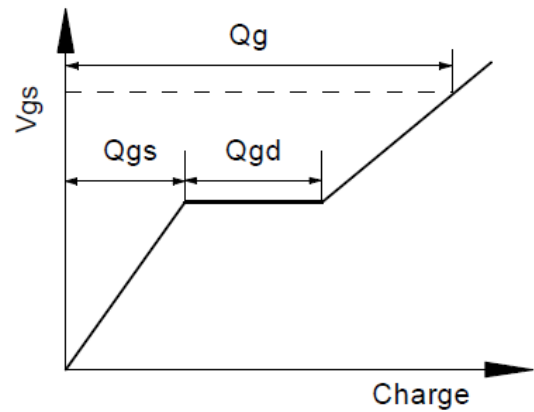


Fig.3-1 Avalanche test circuit

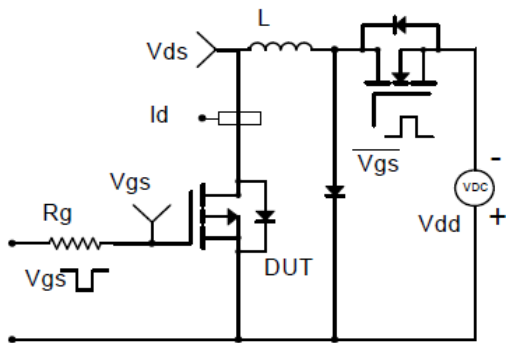
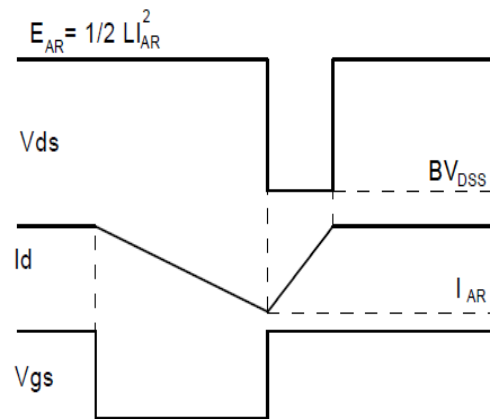


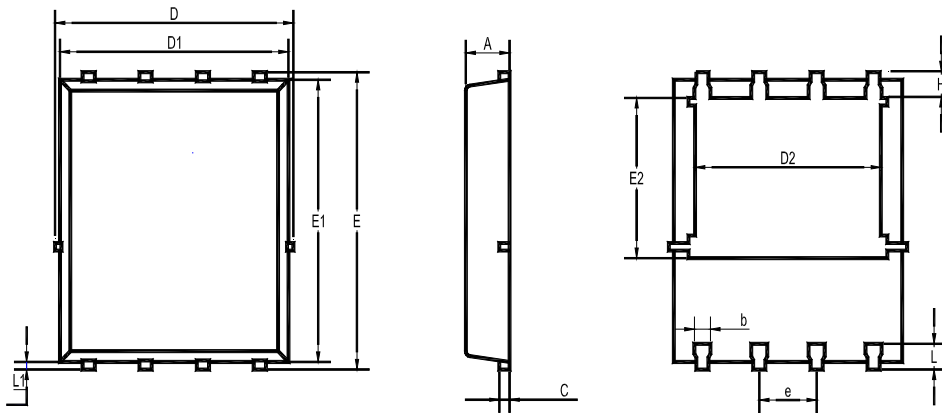
Fig.3-2 Avalanche waveform



WTM503P300LS-HAF

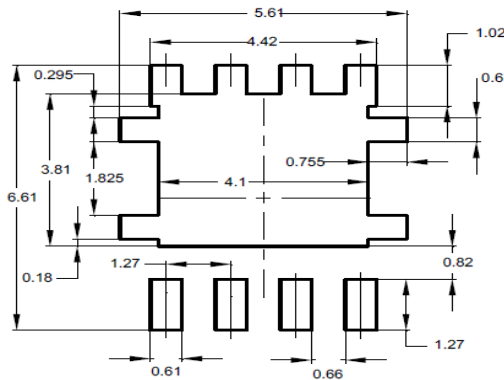
Package Outline Dimensions (Units: mm)

DFN5060



UNIT	A	b	C	D	D1	D2	E	E1	E2	e	L	L1	H
mm	1.12	0.51	0.34	5.26	5.1	4.5	6.25	6	3.66	1.37	0.71	0.2	0.71
	0.9	0.33	0.11	4.7	4.7	3.56	5.75	5.6	3.18	1.17	0.35	0.06	0.35

Recommended Soldering Footprint

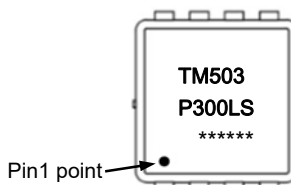


Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
DFN5060	12	8 ± 0.1	0.315 ± 0.004	330	13	3,000

Marking information

- " TM503P300LS " = Part No.
- " ***** " = Date Code Marking
- Font type: Arial



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